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Notice of Allowability	Application No.	Applicant(s)
	10/698,838	HSIEH, IN-CHA
	Examiner David Nhu	Art Unit 2818

-- The MAILING DATE of this communication app ars on the cover she t with th correspondenc address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. This communication is responsive to 10/31/03.
2. The allowed claim(s) is/are 13-24.
3. The drawings filed on 31 October 2003 are accepted by the Examiner.
4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All
 - b) Some*
 - c) None
 of the:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) hereto or 2) to Paper No./Mail Date _____.
 - (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. Notice of References Cited (PTO-892)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date 01
4. Examiner's Comment Regarding Requirement for Deposit
of Biological Material
5. Notice of Informal Patent Application (PTO-152)
6. Interview Summary (PTO-413),
Paper No./Mail Date _____.
7. Examiner's Amendment/Comment
8. Examiner's Statement of Reasons for Allowance
9. Other _____.

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the change and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in an interview with Attorney, Michael D. Schumann, on 6/21/04.

The application has been amended as follows:

Cancel claims 1-12.

*In specifications, page 5, line 18, "silicon-germaium" should be --silicon-germanium--
Page 4, line 26, "Figs. 1 to 6" should be --Figs. 1 to 6 (6a-6b)--*

In claims:

Claims 16, 22, "silicon-germaium" should be --silicon-germanium--

REASONS FOR ALLOWANCE

2. Claims 13-24 are allowed.
3. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 13, 19: a first insulator layer formed on the substrate and the gate layer, wherein the first insulator layer has a flat part, and two vertical walls, the flat part being formed between the two vertical walls; a semiconductor layer formed on the first insulator layer, wherein the semiconductor layer has two channels formed on the two vertical walls, and a first doped area and a second doped area formed to connect with two ends of the two channels respectively, and an intrinsic area formed on the flat part between the

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first doped area and the second doped area; a second insulator layer formed on the semiconductor layer, exposing two sides of the semiconductor layer to form an exposed pattern of the semiconductor layer (as cited in claims 13, 19).

4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Cho (6,458,633 B1): Thin Film Transistor and Method for Fabricating the same.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

David Nhu 

June 21, 2004



DAVID NHU
PRIMARY EXAMINER